

Joanna L Batstone

List of Publications by Year in descending order

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361413

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69
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69
docs citations

69
times ranked

591
citing authors

#	ARTICLE	IF	CITATIONS
1	Opportunities and Challenges of Global Network Cameras. , 2015, , .		0
2	Kinetic Studies of Nanoscale Crystallization in Electronic Materials. Materials Research Society Symposia Proceedings, 1995, 405, 73.	0.1	0
3	Structural and electronic properties of defects in semiconductors. Proceedings Annual Meeting Electron Microscopy Society of America, 1995, 53, 4-5.	0.0	0
4	Microscopic Processes in Crystallisation. Solid State Phenomena, 1994, 37-38, 257-268.	0.3	17
5	Silicide formation and silicide-mediated crystallization of nickel-implanted amorphous silicon thin films. Journal of Applied Physics, 1993, 73, 8279-8289.	2.5	350
6	<i>In situ</i> crystallization of amorphous silicon in the transmission electron microscope. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1993, 67, 51-72.	0.6	59
7	Stability of visible luminescence from porous silicon. Applied Physics Letters, 1993, 62, 2667-2669.	3.3	36
8	High Resolution In Situ TEM Studies of Silicide-Mediated Crystallization of Amorphous Silicon. Materials Research Society Symposia Proceedings, 1993, 321, 579.	0.1	1
9	In situ transmission electron microscopy studies of silicide-mediated crystallization of amorphous silicon. Applied Physics Letters, 1992, 60, 225-227.	3.3	117
10	Stacking fault asymmetry in epitaxial films of <i>mo</i> cvd <i>znse/gaas</i> (001). Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1992, 66, 609-620.	0.6	11
11	Degradation of visible cathodoluminescence from porous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1372-1373.	0.0	0
12	In situ crystallization of amorphous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1346-1347.	0.0	0
13	Dynamic studies of silicide-mediated crystallization of amorphous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1352-1353.	0.0	0
14	The Effect of Rapid Thermal Annealing on Heteroepitaxial Structures. Materials Research Society Symposia Proceedings, 1991, 91, 365.	0.1	4
15	Twin intersections in silicon on sapphire. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1991, 63, 1037-1050.	0.6	11
16	Motion of Crystal/Crystal and Crystal/Amorphous Interfaces. Materials Research Society Symposia Proceedings, 1990, 183, 79.	0.1	0
17	Growth and characterization of ultrathin cobalt silicide films on Si(211) and (311). Journal of Materials Research, 1990, 5, 1032-1041.	2.6	6
18	Interface motion during recrystallization of amorphous NiSi ₂ . Proceedings Annual Meeting Electron Microscopy Society of America, 1990, 48, 524-525.	0.0	1

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19	A crystallographic analysis of the CoSi/Si(111) interface using Transmission Electron Microscopy. Proceedings Annual Meeting Electron Microscopy Society of America, 1990, 48, 574-575.	0.0	0
20	Dependence of the structural and electrical properties of ultrathin cobalt silicide films on formation conditions. Journal of Materials Research, 1989, 4, 144-155.	2.6	16
21	Si _{1-x} CoSi ₂ Structures: Pseudomorphism, Interface Structures, Epitaxial Orientations, and the Control of Pinholes. Journal of the Electrochemical Society, 1989, 136, 815-819.	2.9	22
22	Epitaxial recrystallization and diffusion phenomena in amorphous silicon produced by MeV ion beams. Nuclear Instruments & Methods in Physics Research B, 1989, 37-38, 955-959.	1.4	12
23	Radiation-enhanced diffusion of implanted impurities in amorphous Si. Nuclear Instruments & Methods in Physics Research B, 1989, 39, 343-346.	1.4	7
24	In-situ transmission electron microscopy of NiSi ₂ formation by molecular beam epitaxy. Surface Science, 1989, 208, 317-350.	1.9	47
25	Bonding Configurations at Epitaxial CaF ₂ /Si Interfaces. Materials Research Society Symposia Proceedings, 1989, 139, 351.	0.1	1
26	Reconstruction of (100) Silicon/Disilicide Interfaces. Materials Research Society Symposia Proceedings, 1989, 139, 97.	0.1	2
27	Reconstruction of the NiSi ₂ /Si(100) interface. Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 460-461.	0.0	1
28	Epitaxial films of CoSi ₂ on Si (311) and Si (211). Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 456-457.	0.0	0
29	Origin of A- or B-type NiSi ₂ determined by in situ transmission electron microscopy and diffraction during growth. Physical Review Letters, 1988, 60, 1158-1161.	7.8	50
30	Twin formation and Au segregation during ion beam induced epitaxy of amorphous Si. Applied Physics Letters, 1988, 52, 1043-1045.	3.3	22
31	Control of pinholes in epitaxial CoSi ₂ layers on Si(111). Applied Physics Letters, 1988, 52, 648-650.	3.3	72
32	Trapping of Au in Si during pulsed laser irradiation: A comparison with ion beam induced segregation. Applied Physics Letters, 1988, 53, 2486-2488.	3.3	16
33	Coreless defects and the continuity of epitaxial NiSi ₂ /Si(100) thin films. Applied Physics Letters, 1988, 52, 828-830.	3.3	32
34	Evidence for the influence of interfacial atomic structure on electrical properties at the epitaxial CaF ₂ /Si(111) interface. Physical Review Letters, 1988, 60, 1394-1397.	7.8	84
35	Control of epitaxial orientation of Si on CoSi ₂ (111). Applied Physics Letters, 1988, 52, 1611-1613.	3.3	48
36	Batstone and Phillips Reply. Physical Review Letters, 1988, 61, 2275-2275.	7.8	11

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37	Nonequilibrium segregation and trapping phenomena during ion-induced crystallization of amorphous Si. <i>Physical Review Letters</i> , 1988, 60, 1322-1325.	7.8	49
38	Radiation-enhanced diffusion of Au in amorphous Si. <i>Applied Physics Letters</i> , 1988, 52, 1213-1215.	3.3	38
39	Segregation and Trapping of Gold During Ion-Induced Crystallization of Amorphous Si. <i>Materials Research Society Symposia Proceedings</i> , 1988, 100, 399.	0.1	1
40	Diffusion of Au in Amorphous Si During Ion-Beam Irradiation. <i>Materials Research Society Symposia Proceedings</i> , 1988, 100, 87.	0.1	1
41	New Directions in the Growth of Epitaxial Insulators and Metals on Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1988, 116, 403.	0.1	2
42	Growth of Thin Epitaxial CoSi_2 Layers on Si(100). <i>Materials Research Society Symposia Proceedings</i> , 1988, 116, 439.	0.1	25
43	The Effect of Rapid Thermal Annealing on the Dislocation Structure of Silicon on Sapphire. <i>Materials Research Society Symposia Proceedings</i> , 1988, 138, 373.	0.1	10
44	TEM and cathodoluminescence of precipitates in II-VI semiconductors. <i>Proceedings Annual Meeting Electron Microscopy Society of America</i> , 1988, 46, 488-489.	0.0	0
45	Subboundary-free zone-melt recrystallization of thin-film silicon. <i>Applied Physics Letters</i> , 1987, 51, 1256-1258.	3.3	42
46	Mechanisms of buried oxide formation by ion implantation. <i>Applied Physics Letters</i> , 1987, 50, 19-21.	3.3	77
47	Nucleation and Growth of Ultrathin Epitaxial Metal Silicides on Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1987, 102, 253.	0.1	0
48	Ultrathin Single Crystal CoSi_2 Layers on Si(111) and Si(100). <i>Materials Research Society Symposia Proceedings</i> , 1987, 102, 265.	0.1	10
49	In-Situ Rapid Thermal Annealing of Heterostructures Grown by Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1987, 102, 355.	0.1	2
50	Hot Electron Transistors Using Si/ CoSi_2 . <i>Materials Research Society Symposia Proceedings</i> , 1987, 102, 361.	0.1	6
51	The Effect of Formation Conditions on the Structural and Electrical Properties of Ultrathin Cobalt Silicide Films. <i>Materials Research Society Symposia Proceedings</i> , 1987, 102, 389.	0.1	1
52	Effect of Atomic Structure at the Epitaxial CaF_2 /Si(111) Interface on Electrical Properties. <i>Materials Research Society Symposia Proceedings</i> , 1987, 102, 45.	0.1	3
53	In-Situ Rapid Thermal Annealing of Heterostructures Grown by Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1987, 107, 253.	0.1	0
54	Hot Electron Transistors Using Si/ CoSi_2 . <i>Materials Research Society Symposia Proceedings</i> , 1987, 107, 259.	0.1	7

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55	Techniques of Insulator/Semiconductor Heterostructure Specimen Preparation. Materials Research Society Symposia Proceedings, 1987, 115, 63.	0.1	5
56	Electrical Transport in Ultrathin Films of CoSi_2 on Si(111). Materials Research Society Symposia Proceedings, 1987, 91, 427.	0.1	2
57	Characterization of Ultrathin CoSi_2 on Si(111) Layers.. Materials Research Society Symposia Proceedings, 1987, 91, 445.	0.1	15
58	In-Situ Studies of the MBE Growth of CoSi_2 on Si (111) in a UHV Transmission Electron Microscope. Materials Research Society Symposia Proceedings, 1987, 94, 151.	0.1	0
59	In-situ study of the molecular beam epitaxy of CoSi_2 on (111)-Si by transmission electron microscopy and diffraction. Applied Physics Letters, 1987, 51, 45-47.	3.3	81
60	Electrical and structural characterization of ultrathin epitaxial CoSi_2 on Si(111). Applied Physics Letters, 1987, 51, 1895-1897.	3.3	51
61	Rapid thermal processing to improve the epitaxy of (100)-silicon on (111,02) sapphire. Applied Physics Letters, 1987, 50, 466-468.	3.3	15
62	High-resolution electron microscopy of interfaces and surfaces. Ultramicroscopy, 1987, 22, 35-46.	1.9	17
63	The Role of Implant Temperature in the Formation of Thin Buried Oxide Layers. Materials Research Society Symposia Proceedings, 1986, 74, 585.	0.1	4
64	Microstructural Characterization of High Dose Oxygen Implanted Silicon. Materials Research Society Symposia Proceedings, 1986, 74, 597.	0.1	3
65	Electron Transport Through Epitaxial Metal/Semiconductor Heterostructures. Materials Research Society Symposia Proceedings, 1986, 77, 271.	0.1	4
66	Correlation of Electrical Properties with Structure Imaging of Semiconductor Interfaces. Materials Research Society Symposia Proceedings, 1986, 82, 335.	0.1	3
67	Dislocation Luminescence in ZnSe. Proceedings Annual Meeting Electron Microscopy Society of America, 1986, 44, 818-819.	0.0	2
68	Atomic structure imaging of the Si/SiO ₂ interface with high-resolution electron microscopy. Proceedings Annual Meeting Electron Microscopy Society of America, 1986, 44, 390-391.	0.0	2
69	Luminescence studies of individual dislocations in II-VI (ZnSe) and III-V (InP) semiconductors. Journal of Physics C: Solid State Physics, 1984, 17, 6477-6492.	1.5	94